

Reactor: **Cambridge Savannah**
 Date: **24-Jul-19**

 Growth: Al₂O₃ on 4" Silicon wafer
 Expected growth rate: 0.9-1.3 Angstrom per cycle
 Expected Refractive Index: 1.7 n

 Recipe name: 1 Al₂O₃_200_10nm_O3-??Acyc
 Growth Temperature: 200 °C
 Precursor: TMA

 Number of Cycles: 200 Cycles

 Gaertner Angstroms grown: 191.59 Angstroms
 Gaertner Refractive Index: 1.7662 n
 Gaertner Growth Rate: 0.96 Angstrom/ Cycle

 VASE Thickness: 0.00 Angstroms
 VASE MSE: 0 MSE
 VASE Refractive index: 0.0000 n
 VASE Growth Rate: 0.00 Angstrom/ Cycle

Gaertner Measurements	Thickness (A)	R.I. (n)
Top Left	190.70	1.7640
Top Right	192.39	1.7665
Center	191.32	1.7703
Bottom left	192.63	1.7670
Bottom Right	190.90	1.7632
Average:	191.59	1.7662

Recipe Information

Dose Time: 20 milliseconds
 Dose Purge Time: 7 seconds
 Dose purge Ar Flow: 20 sccm

 O3 Dose Time: 1000 milliseconds
 O3 Purge Time: 15 Seconds
 O3 Purge Ar Flow: 20 sccm

 Precursor Jacket temp (Oven): N/A °C

Note: 0.12 Liters per minute Ozone